Abstracts

Impedance of GaAs P-I-N Diodes

A. Gopinath. "Impedance of GaAs P-I-N Diodes." 1988 MTT-S International Microwave Symposium Digest 88.2 (1988 Vol. II [MWSYM]): 801-802.

A computer model of GaAs p-i-n diodes shows that when the i-layer thickness is greater than about four times the diffusion length, diode forward resistance may be high. Comparison with measured I-V characteristics suggest that diodes now have i-layers with lifetimes of about 10-/sup 7/s.

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